

Mechanical Data

	Die Size(mm×mm)		0.340×0.230(包含划片道)	
	Die Thickness(μm)		635±10	
	Scribe Line(μm)		40	
	Bonding PAD Size(μm ²)	Top	80×80	
	Cathode (Top)	Metallization	Al	
		Thickness(μm)	1.5 ±0.1	
	Anode (Bottom)	Metallization		
	Die Bonding Requirement (Recommendation)			
	Wafer Size(mm)		φ150	
	Wire Bonding Requirement (Recommendation)		1 Cu Wire, φ20μm	

Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{RWM}				20	V
Holding Voltage	V_H	$I_T=I_H$		3.0	3.5	V
Holding Current	I_H		35			mA
Reverse Leakage Current	I_R	$V_{RWM}=20V, T=25^{\circ}C$			500	nA
Clamping Voltage	V_C	$I_{PP}=4A, t_p=8/20\mu s$			8	V
Trigger Voltage	V_T			24		V
Junction Capacitance	C_j	$V_R = 0V, f = 1MHz$		0.45	0.65	pF

NOTICE

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